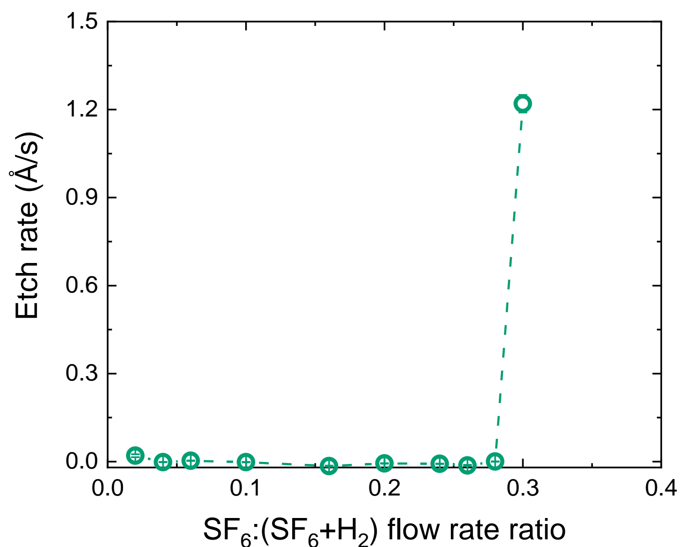

Figure 1: Continuous etch rate of MoS_2 for different ratios of SF_6 and H_2 in the plasma. Below a ratio of 0.3 there is no continuous etching. In the ALE process a ratio of 0.26 was used.

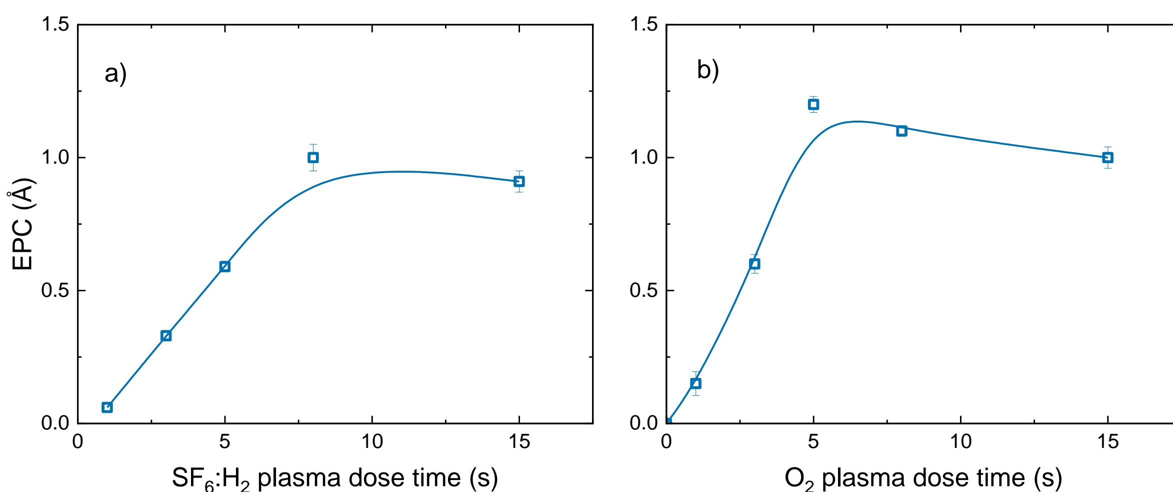

Figure 2: Saturation curves for a) $SF_6/H_2/Ar$ plasma step (O_2 plasma time is kept at 10 s) and b) O_2 plasma step ($SF_6/H_2/Ar$ plasma time is kept at 10 s). Lines serve as a guide to the eye.

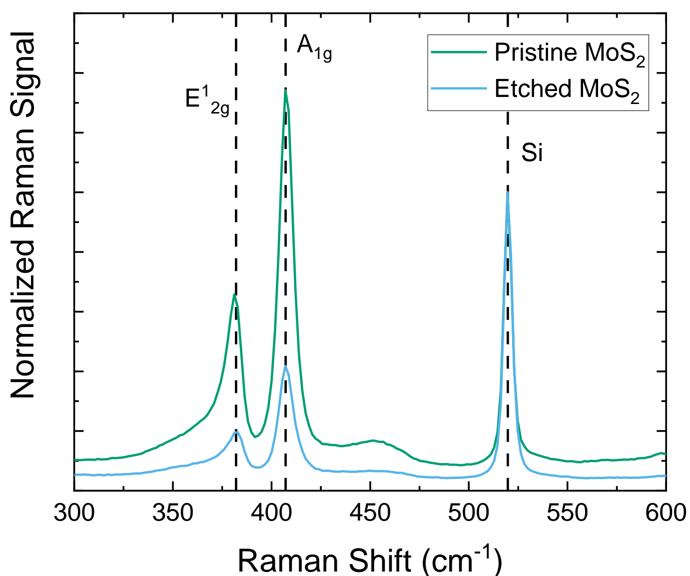

Figure 3: Raman spectra of pristine MoS_2 and MoS_2 etched with 20 cycles of ALE using 8 s SF_6-based plasma and 10 s O_2 plasma exposures. Spectra are normalized to the Si peak.